

ABSTRACT

An adhesive film for semiconductor, which comprises at least one resin layer, and, after bonded to a lead frame, has at 25°C a 90°-peel strength of at least 5 N/m between the resin layer and the lead frame, and, after a lead frame is bonded to the adhesive film for semiconductor and sealed with a sealing material, has at least at one point of temperatures ranging from 0 to 250°C a 90°-peel strength of at most 1000 N/m between the resin layer and each of the lead frame and the sealing material; a lead frame and a semiconductor device using the adhesive film for semiconductor; and a method of producing a semiconductor device.